# **Switching Transistor**

## **PNP Silicon**

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	-40	Vdc
Collector – Base Voltage	V <sub>CBO</sub>	-40	Vdc
Emitter-Base Voltage	$V_{\text{EBO}}$	-5.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	-600	mAdc
Collector Current – Peak	I <sub>CM</sub>	-900	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) @T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

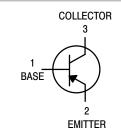
\*Transient pulses must not cause the junction temperature to be exceeded. 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.

2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



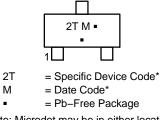
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#### MARKING DIAGRAM



(Note: Microdot may be in either location)

\*Specific Device Code, Date Code or overbar orientation and/or location may vary depending upon manufacturing location. This is a representation only and actual devices may not match this drawing exactly.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBT4403LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBT4403LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT4403LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage	(Note 3) $(I_{C} = -1.0 \text{ mAdc}, I_{B} = 0)$	V <sub>(BR)CEO</sub>	-40	-	Vdc
Collector-Base Breakdown Voltage	$(I_{C} = -0.1 \text{ mAdc}, I_{E} = 0)$	V <sub>(BR)CBO</sub>	-40	-	Vdc
Emitter-Base Breakdown Voltage	$(I_{E} = -0.1 \text{ mAdc}, I_{C} = 0)$	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Base Cutoff Current	$(V_{CE} = -35 \text{ Vdc}, \text{ V}_{EB} = -0.4 \text{ Vdc})$	I <sub>BEV</sub>	-	-0.1	μAdc
Collector Cutoff Current	$(V_{CE} = -35 \text{ Vdc}, \text{ V}_{EB} = -0.4 \text{ Vdc})$	I <sub>CEX</sub>	-	-0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) (Note 3)		h <sub>FE</sub>	30 60 100 100 20	- - 300 -	_
Collector – Emitter Saturation Voltage	Note 3) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)	V <sub>CE(sat)</sub>		-0.4 -0.75	Vdc
Base-Emitter Saturation Voltage (Not	e 3) (I <sub>C</sub> = -150 mAdc, I <sub>B</sub> = -15 mAdc) (I <sub>C</sub> = -500 mAdc, I <sub>B</sub> = -50 mAdc)	V <sub>BE(sat)</sub>	-0.75 -	-0.95 -1.3	Vdc
SMALL-SIGNAL CHARACTERISTIC	S		-	•	
Current-Gain - Bandwidth Product	$(I_{C} = -20 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 100 \text{ MHz})$	f <sub>T</sub>	200	-	MHz
Collector-Base Capacitance	(V <sub>CB</sub> = -10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		-	8.5	pF
Emitter-Base Capacitance	itter–Base Capacitance $(V_{BE} = -0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		-	30	pF
Input Impedance	npedance $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		1.5	15	kΩ
Voltage Feedback Ratio	ltage Feedback Ratio $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		0.1	8.0	X 10-4
Small-Signal Current Gain	nall-Signal Current Gain $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		60	500	-
Dutput Admittance $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h <sub>oe</sub>	1.0	100	μMhos
SWITCHING CHARACTERISTICS					
Delay Time	(V <sub>CC</sub> = -30 Vdc, V <sub>EB</sub> = -2.0 Vdc,	t <sub>d</sub>	-	15	-
Rise Time	$I_{\rm C} = -150 \text{ mAdc}, I_{\rm B1} = -15 \text{ mAdc})$	t <sub>r</sub>	-	20	ns
Storage Time	$(V_{CC} = -30 \text{ Vdc}, I_C = -150 \text{ mAdc},$	ts	-	225	ne
Fall Time	$I_{B1} = I_{B2} = -15 \text{ mAdc}$	+.		20	ns

Fall Time t<sub>f</sub> Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

 $I_{B1} = I_{B2} = -15 \text{ mAdc}$ 

3. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

#### SWITCHING TIME EQUIVALENT TEST CIRCUIT

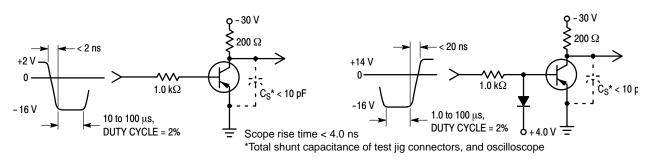


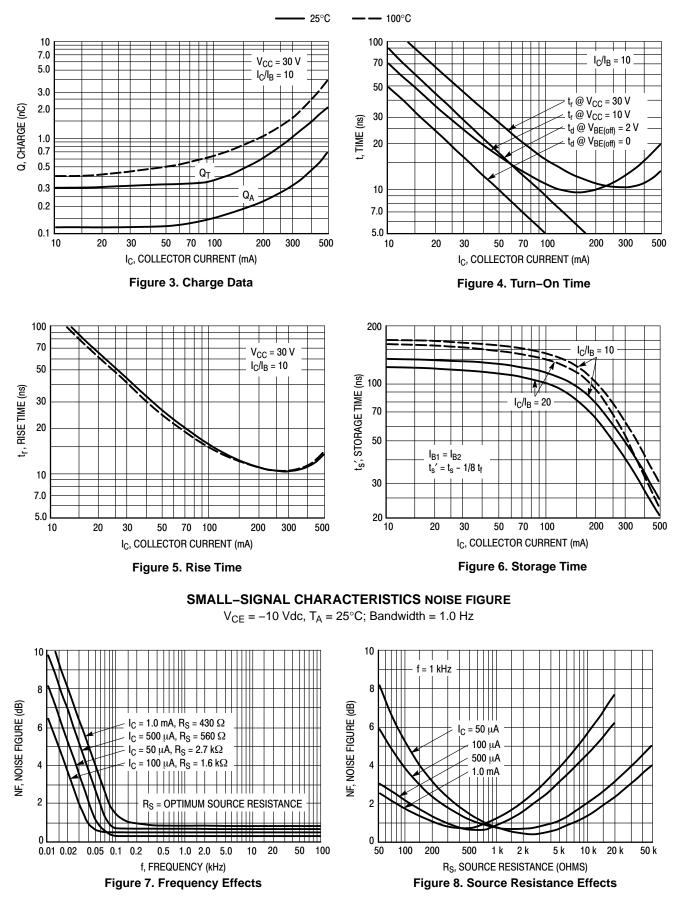
Figure 1. Turn-On Time

Figure 2. Turn-Off Time

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30

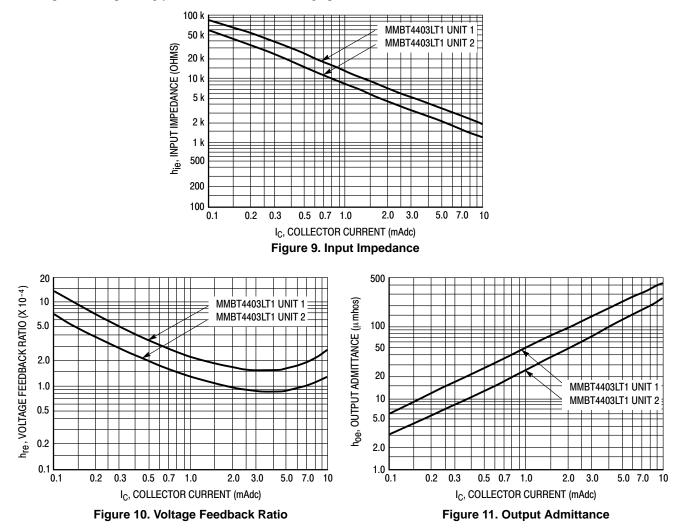
#### **TRANSIENT CHARACTERISTICS**



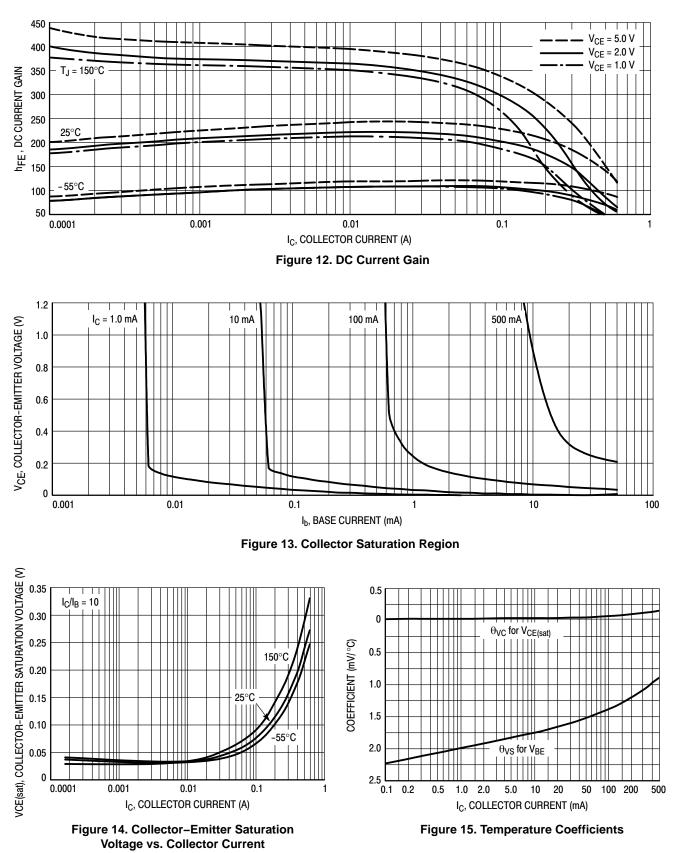
#### h PARAMETERS

### $V_{CE}$ = 10 Vdc, f = 1.0 kHz, T<sub>A</sub> = 25°C

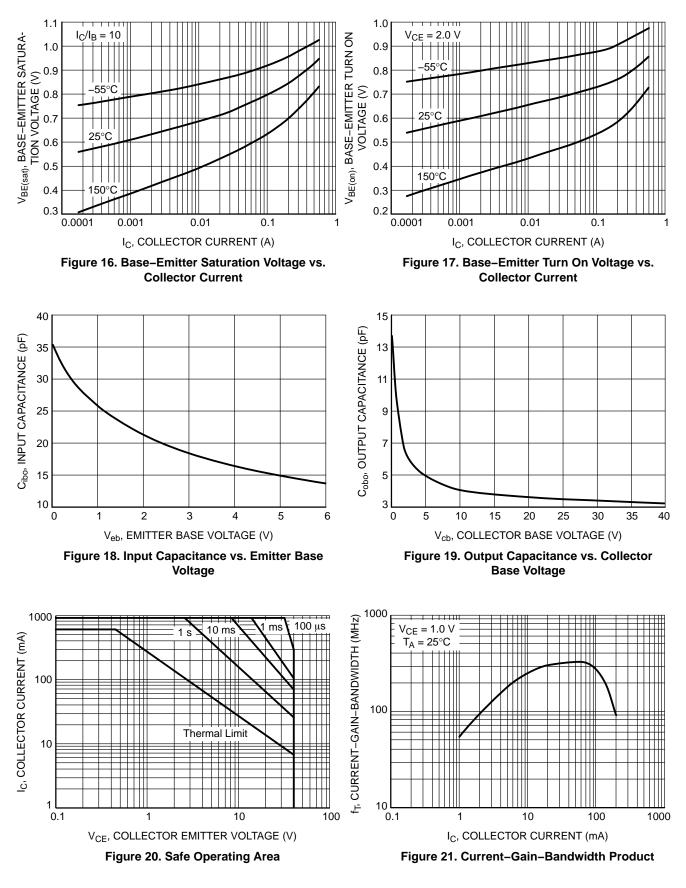
This group of graphs illustrates the relationship between  $h_{fe}$  and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.



#### STATIC CHARACTERISTICS



### STATIC CHARACTERISTICS



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